# PBSS5112PAP

# 120 V, 1 A PNP/PNP low VCEsat (BISS) transistor 30 November 2012 Prod

**Product data sheet** 

# 1. Product profile

#### 1.1 General description

PNP/PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package. NPN/PNP complement: PBSS4112PANP. NPN/NPN complement: PBSS4112PAN.

#### 1.2 Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- · Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

#### 1.3 Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-120	V
I <sub>C</sub>	collector current			-	-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	-1.5	Α
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-	-7	V
Per transistor	Per transistor						
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C		-	-	440	mΩ



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# **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		P
3	C2	collector TR2	7 8	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	1 2 3	E1 B1 C2
6	C1	collector TR1	Transparent top view  DFN2020-6 (SOT1118)	sym138
7	C1	collector TR1	DI 112020-0 (0011110)	
8	C2	collector TR2		

# **Ordering information**

Table 3. **Ordering information** 

Type number	Package			
	Name	Description	Version	
PBSS5112PAP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118	

#### **Marking** 4.

Table 4. **Marking codes** 

Type number	Marking code
PBSS5112PAP	2S

#### **Limiting values 5**.

#### Table 5. **Limiting values**

PBSS5112PAP

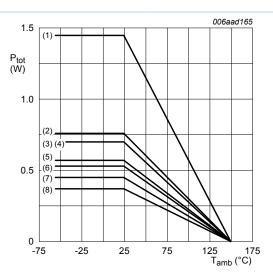
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transistor					
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-120	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-120	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-7	V
I <sub>C</sub>	collector current		-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-1.5	Α
I <sub>B</sub>	base current		-	-0.3	А

Symbol	Parameter	Conditions	l l	Min	Max	Unit
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
			[5]	-	450	mW
			[6]	-	760	mW
			[7]	-	700	mW
			[8]	-	1450	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
			[5]	-	620	mW
			[6]	-	1040	mW
			[7]	-	960	mW
		[8]	-	2000	mW	
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35  $\mu m$  copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- 6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

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- (1) 4-layer PCB 70 μm, mounting pad for collector 1 cm<sup>2</sup>
- (2) FR4 PCB 70 µm, mounting pad for collector 1 cm<sup>2</sup>
- (3) 4-layer PCB 70 µm, standard footprint
- (4) 4-layer PCB 35 μm, mounting pad for collector 1 cm<sup>2</sup>
- (5) FR4 PCB 35  $\mu m$ , mounting pad for collector 1 cm<sup>2</sup>
- (6) 4-layer PCB 35 µm, standard footprint
- (7) FR4 PCB 70 µm, standard footprint
- (8) FR4 PCB 35 µm, standard footprint

Fig. 1. Per transistor: power derating curves

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						,
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	338	K/W
	from junction to ambient		[2]	-	-	219	K/W
	ambient		[3]	-	-	236	K/W
		[4]	[4]	-	-	179	K/W
		[ <u>5</u> ]	[5]	-	-	278	K/W
			-	-	164	K/W	
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	30	K/W

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device				'			
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	245	K/W
	from junction to		[2]	-	-	160	K/W
	ambient		[3]	-	-	171	K/W
		[4] [5]	[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

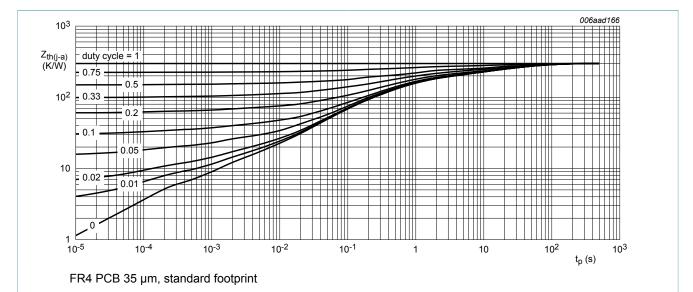
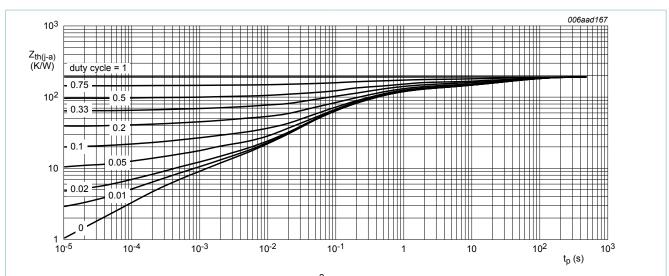


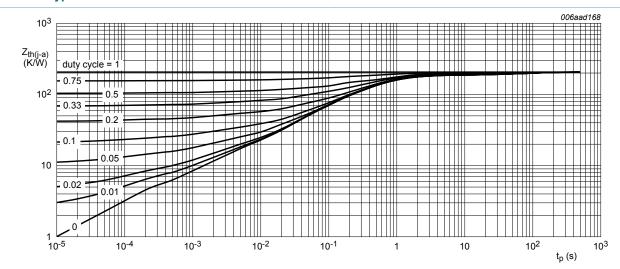
Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

5/17



FR4 PCB 35 µm, mounting pad for collector 1 cm<sup>2</sup>

Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 35 µm, standard footprint

Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

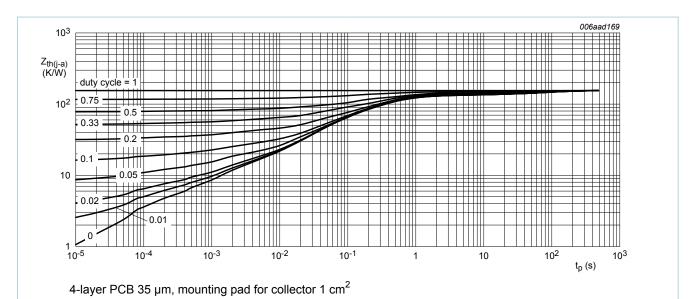
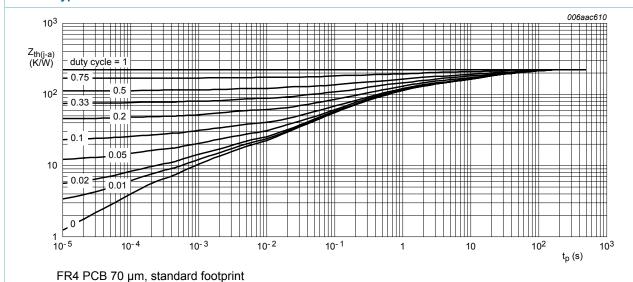


Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; Fig. 6. typical values

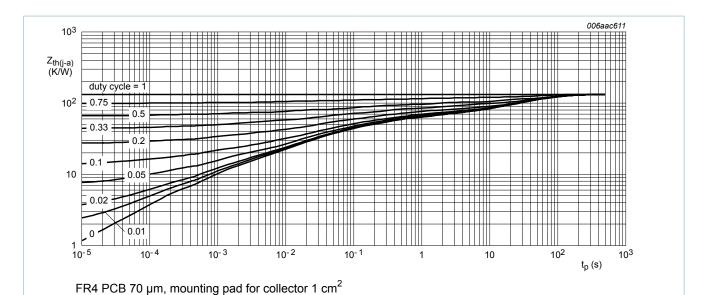


Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

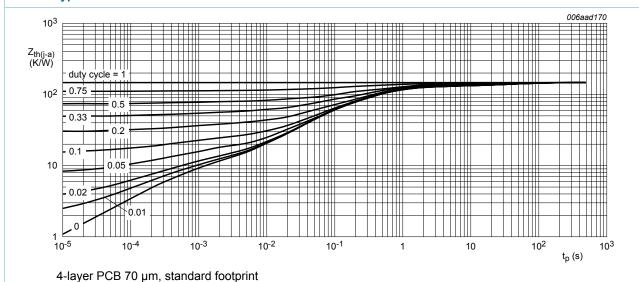


Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

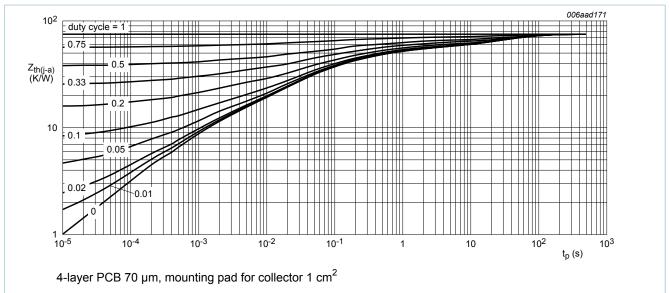


Fig. 9. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
Per transist	tor						
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -96 V; $I_E$ = 0 A; $T_{amb}$ = 25 °C	-	•	-	-100	nA
	current	$V_{CB} = -96 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	•	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	1	190	305	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	5	50	85	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	1	15	25	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-150	-220	mV
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-	-335	-480	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-		-	440	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; $T_{amb}$ = 25 °C	-	-	-	-1	V

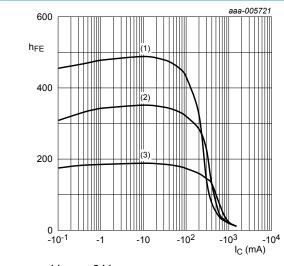
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#### 120 V, 1 A PNP/PNP low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-0.9	V
t <sub>d</sub>	delay time	$V_{CC} = -10 \text{ V}; I_C = -500 \text{ mA};$	-	15	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = -25 \text{ mA}; I_{Boff} = 25 \text{ mA};$	-	245	-	ns
t <sub>on</sub>	turn-on time	T <sub>amb</sub> = 25 °C	-	260	-	ns
ts	storage time		-	290	-	ns
t <sub>f</sub>	fall time		-	270	-	ns
t <sub>off</sub>	turn-off time		-	560	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	50	100	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	9.5	13	pF



 $V_{CE} = -2 V$ 

(1)  $T_{amb}$  = 100 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55$  °C

Fig. 10. DC current gain as a function of collector current; typical values

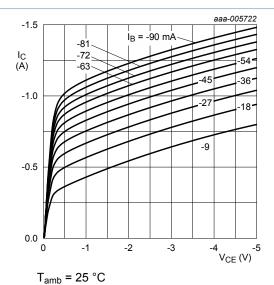
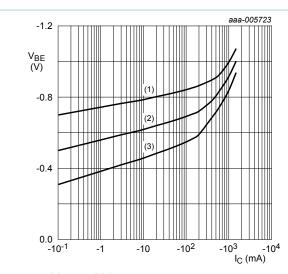


Fig. 11. Collector current as a function of collectoremitter voltage; typical values



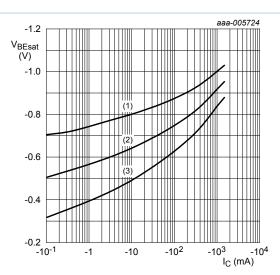
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 12. Base-emitter voltage as a function of collector current; typical values



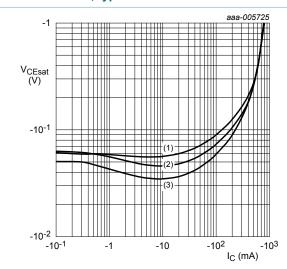
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 13. Base-emitter saturation voltage as a function of collector current; typical values



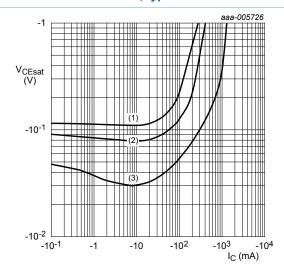
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values



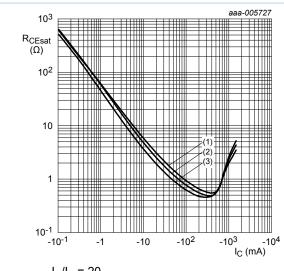
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation voltage as a function of collector current; typical values

#### 120 V, 1 A PNP/PNP low VCEsat (BISS) transistor



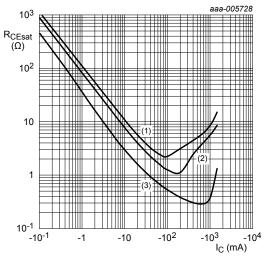
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55$$
 °C

Fig. 16. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

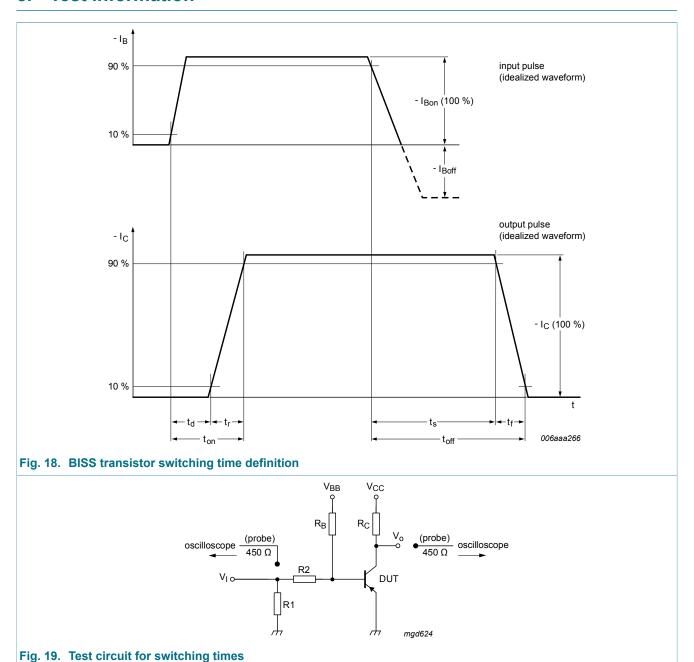
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 17. Collector-emitter saturation resistance as a function of collector current; typical values

**Product data sheet** 

# 8. Test information

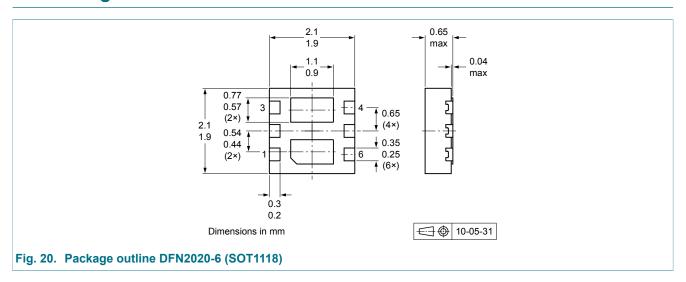


# 8.1 Quality information

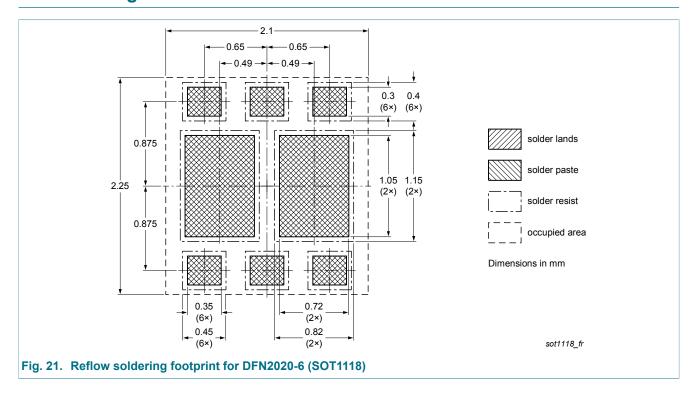
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 9. Package outline



# 10. Soldering



# 11. Revision history

Table 8. Revision history

······································							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS5112PAP v.1	20121130	Product data sheet	-	-			

PBSS5112PAP All informa

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# 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### 120 V, 1 A PNP/PNP low VCEsat (BISS) transistor

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